

RF Power Field-Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. Dual path topology suitable for Doherty, quadrature, single-ended and push-pull applications.

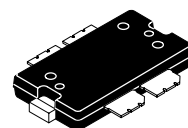
- Typical 2-Carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 500$ mA, $P_{out} = 10$ Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
Power Gain — 14.5 dB
Drain Efficiency — 25.5%
IM3 @ 10 MHz Offset — -37 dBc in 3.84 MHz Channel Bandwidth
ACPR @ 5 MHz Offset — -39 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 2140 MHz, 45 Watts CW Output Power

Features

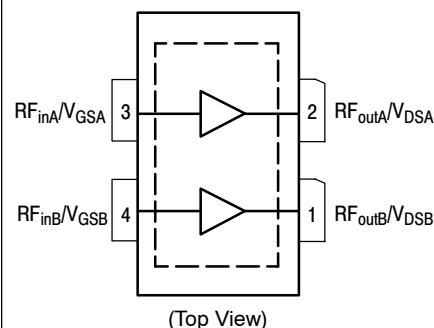
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- 200°C Capable Plastic Package
- RoHS Compliant
- In Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.

MRF5P21045NR1

**2110-2170 MHz, 10 W AVG., 28 V
2 x W-CDMA, DUAL PATH
LATERAL N-CHANNEL
RF POWER MOSFET**



**CASE 1486-03, STYLE 1
TO-270 WB-4**



Note: Exposed backside of the package is the source terminal for the transistors.

Figure 1. Pin Connections

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	- 0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	- 0.5, +15	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.35	°C/W
Case Temperature 80°C, 45 W CW		1.48	
Case Temperature 77°C, 10 W CW			

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

Table 5. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics ⁽¹⁾

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics ⁽¹⁾

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 120\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	2	—	3.5	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 500\text{ mAdc}$)	$V_{GS(Q)}$	—	3.8	—	Vdc
Fixture Gate Quiescent Voltage ⁽²⁾ ($V_{DD} = 28\text{ Vdc}$, $I_D = 500\text{ mAdc}$, Measured in Functional Test)	$V_{GG(Q)}$	6	7.6	10	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.2\text{ Adc}$)	$V_{DS(on)}$	0.2	0.3	0.35	Vdc

Dynamic Characteristics ^(1,3)

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	0.9	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	124	—	pF
Input Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{iss}	—	247	—	pF

Functional Tests ⁽¹⁾ (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 500\text{ mA}$, $P_{out} = 10\text{ W Avg.}$, $f_1 = 2112.5\text{ MHz}$, $f_2 = 2122.5\text{ MHz}$ and $f_1 = 2157.5\text{ MHz}$, $f_2 = 2167.5\text{ MHz}$, 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset. IM3 measured in 3.84 MHz Bandwidth @ $\pm 10\text{ MHz}$ Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	13.5	14.5	16.5	dB
Drain Efficiency	η_D	23.5	25.5	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-39	-37	dBc
Input Return Loss	IRL	—	-12	-8	dB

1. Measurement made with device in single-ended configuration. (See Figure 4, Possible Circuit Topologies)
2. $V_{GG} = 2 \times V_{GS(Q)}$. Parameter measured on Freescale Test Fixture, due to resistive divider network on the board. Refer to Test Circuit schematic.
3. Part internally matched both on input and output.

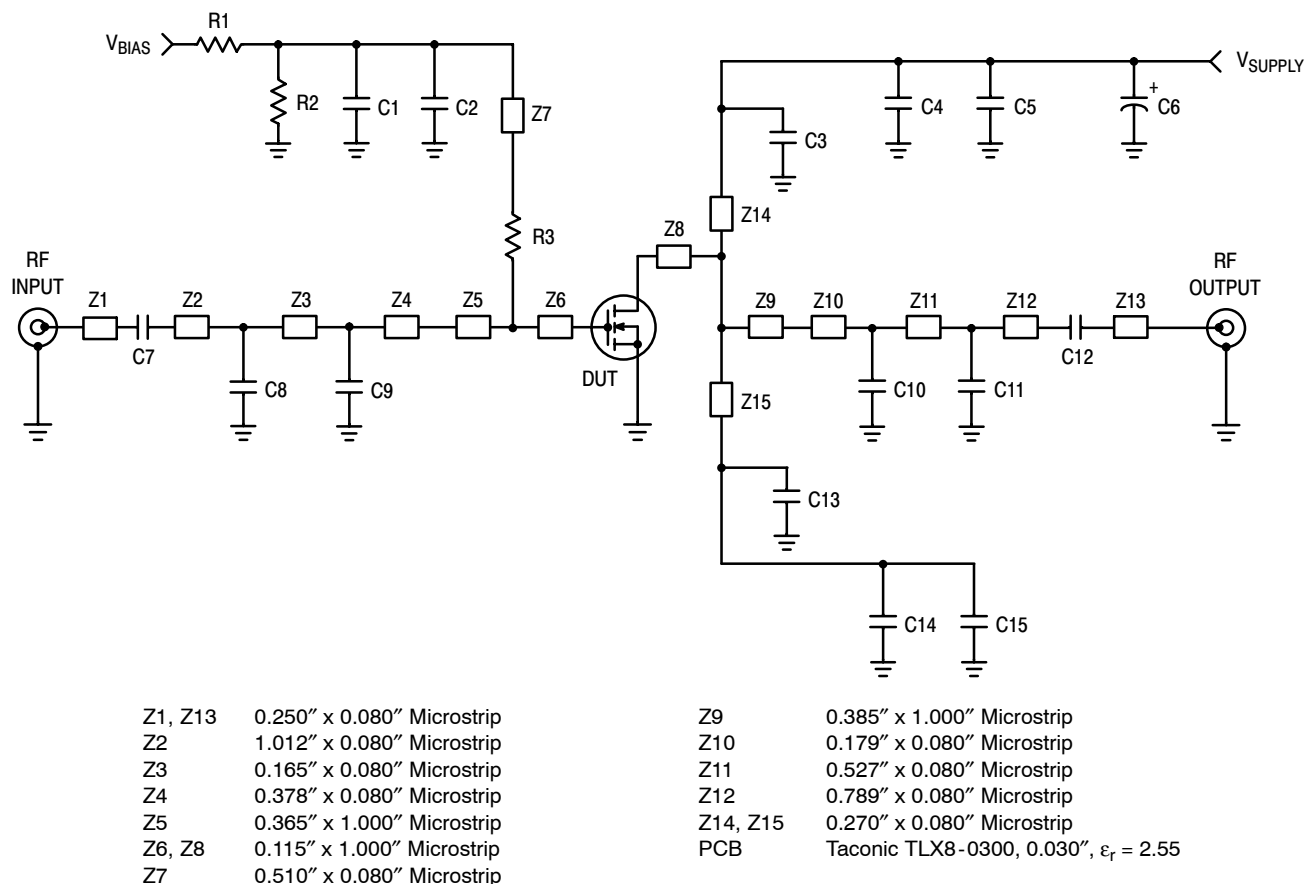


Figure 2. MRF5P21045NR1 Test Circuit Schematic — Single-Ended Configuration

Table 6. MRF5P21045NR1 Test Circuit Component Designations and Values — Single-Ended Configuration

Part	Description	Part Number	Manufacturer
C1	220 nF Chip Capacitor	18125C224KAT4A	AVX
C2, C3, C7, C12, C13	6.8 pF Chip Capacitors	ATC100B6R8BT500XT	ATC
C4, C5, C14, C15	6.8 μ F Chip Capacitors	C4532X5R1H685MT	TDK
C6	220 μ F, 63 V Electrolytic Capacitor, Radial	EMVY630ATR221MKE0S	Nippon Chemi-Con
C8, C10	1 pF Chip Capacitors	ATC100B1R0BT500XT	ATC
C9	1.5 pF Chip Capacitor	ATC100B1R5BT500XT	ATC
C11	0.5 pF Chip Capacitor	ATC100B0R5BT500XT	ATC
R1, R2	10 k Ω , 1/4 W Chip Resistors	CRCW12061001FKTA	Vishay
R3	10 Ω , 1/4 W Chip Resistor	CRCW120610R0FKTA	Vishay

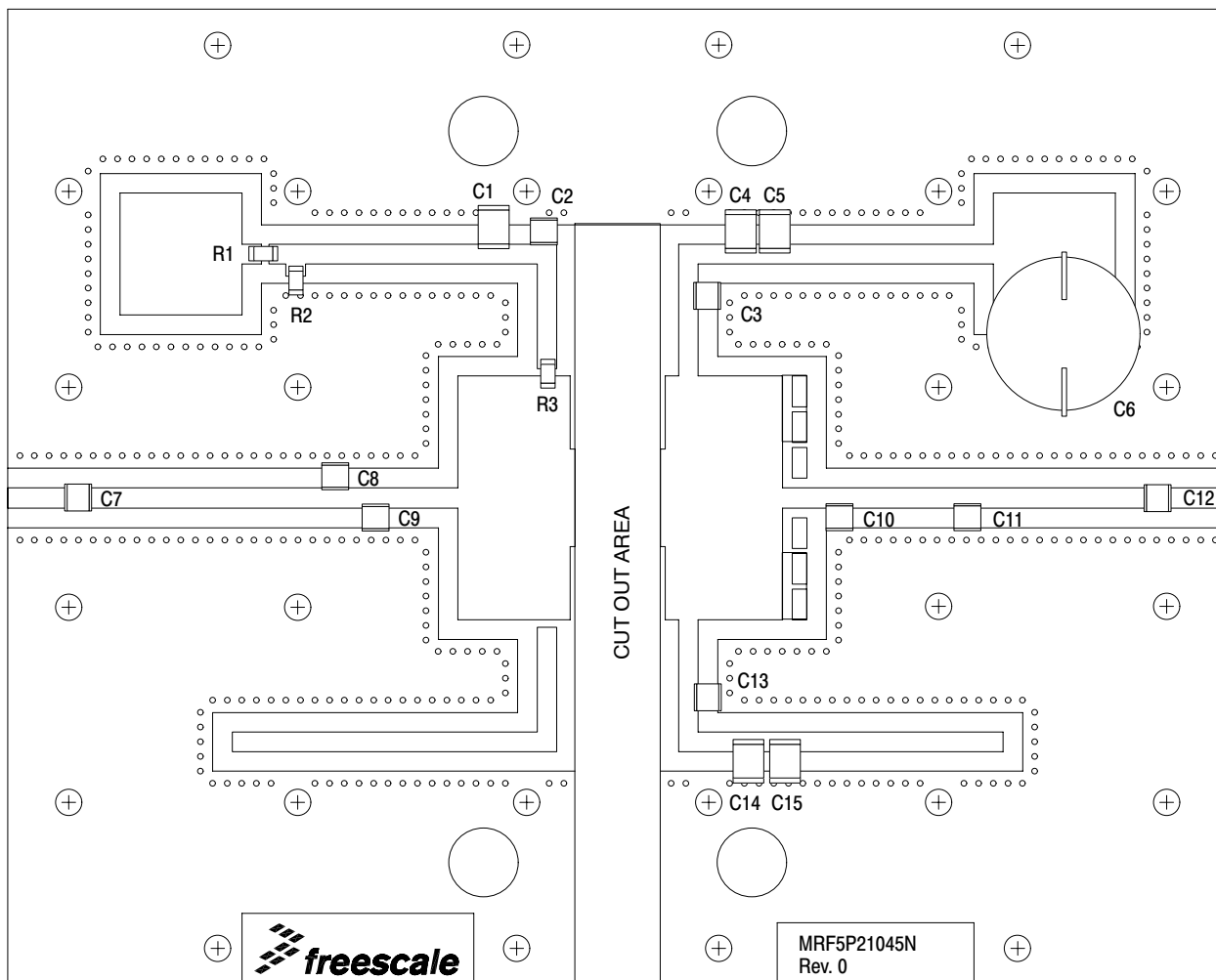


Figure 3. MRF5P21045NR1 Test Circuit Component Layout — Single-Ended Configuration

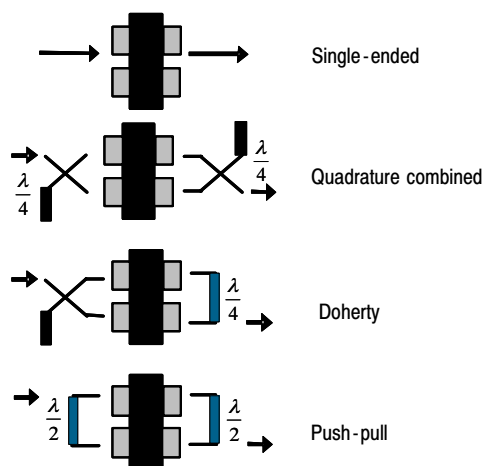
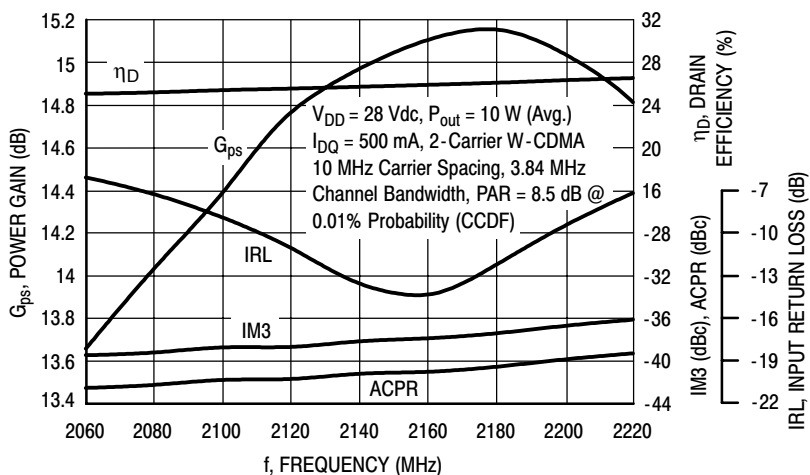
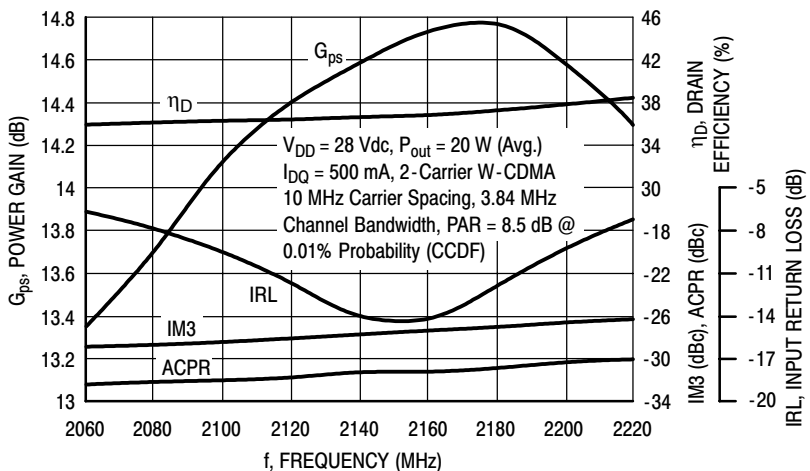


Figure 4. Possible Circuit Topologies

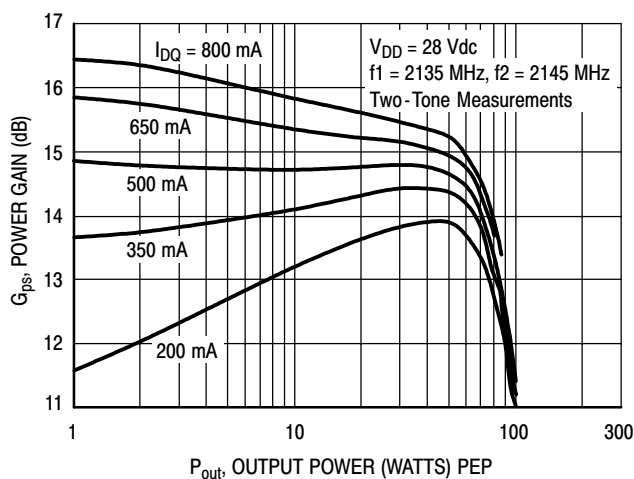
TYPICAL CHARACTERISTICS



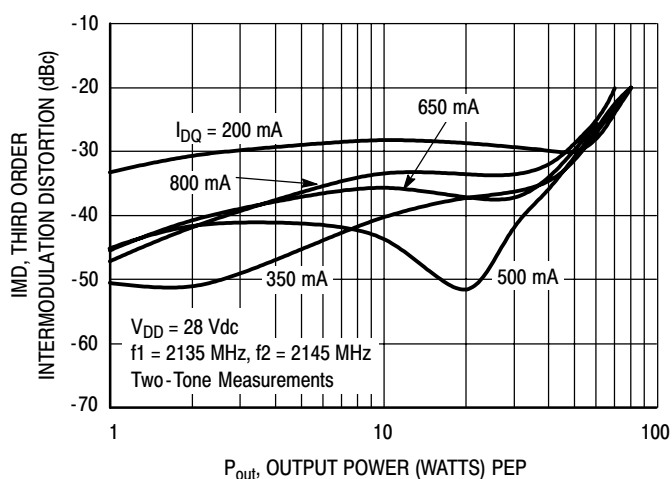
**Figure 5. 2-Carrier W-CDMA Broadband Performance
@ $P_{out} = 10$ Watts Avg.**



**Figure 6. 2-Carrier W-CDMA Broadband Performance
@ $P_{out} = 20$ Watts Avg.**



**Figure 7. Two-Tone Power Gain versus
Output Power**



**Figure 8. Third Order Intermodulation Distortion
versus Output Power**

TYPICAL CHARACTERISTICS

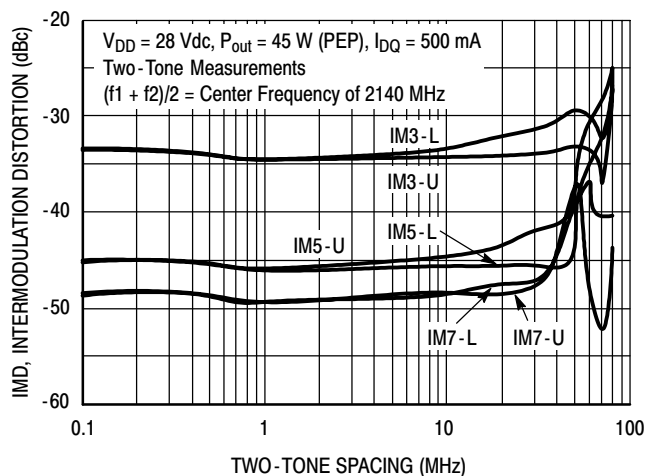


Figure 9. Intermodulation Distortion Products versus Tone Spacing

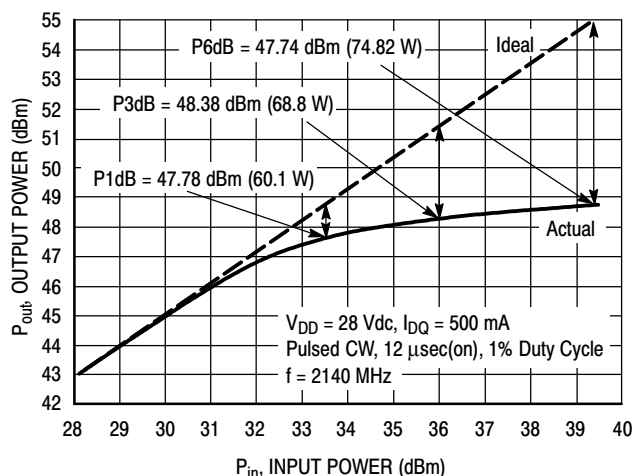


Figure 10. Pulsed CW Output Power versus Input Power

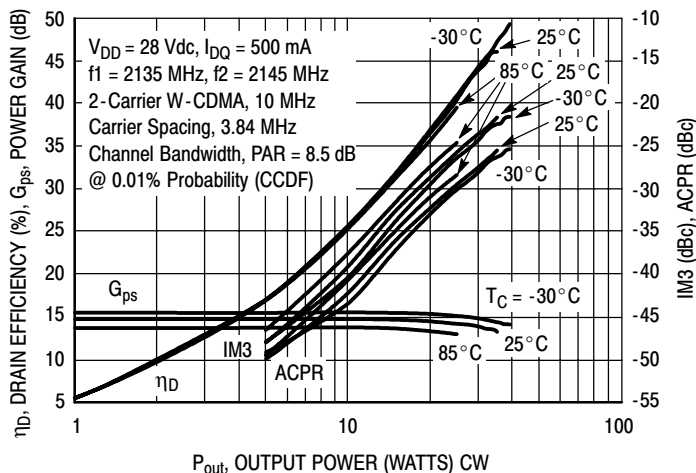


Figure 11. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

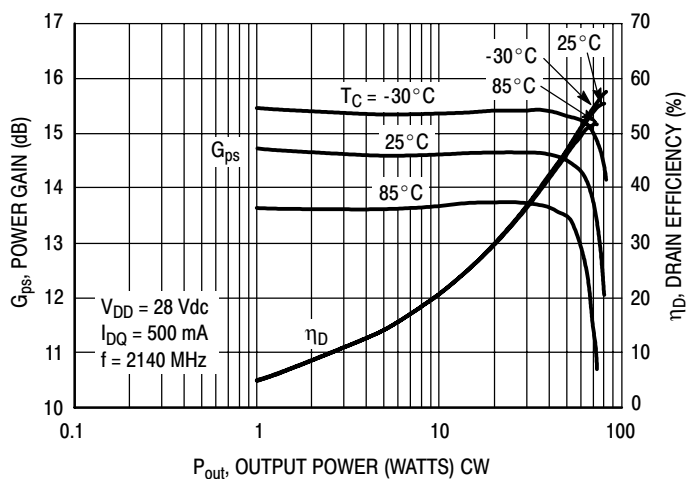


Figure 12. Power Gain and Drain Efficiency versus CW Output Power

TYPICAL CHARACTERISTICS

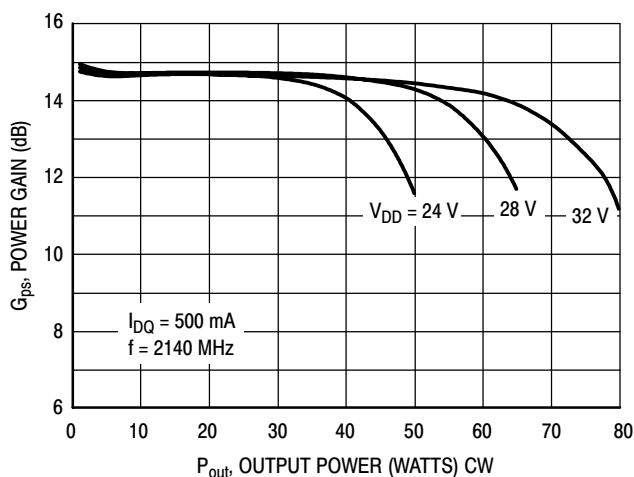
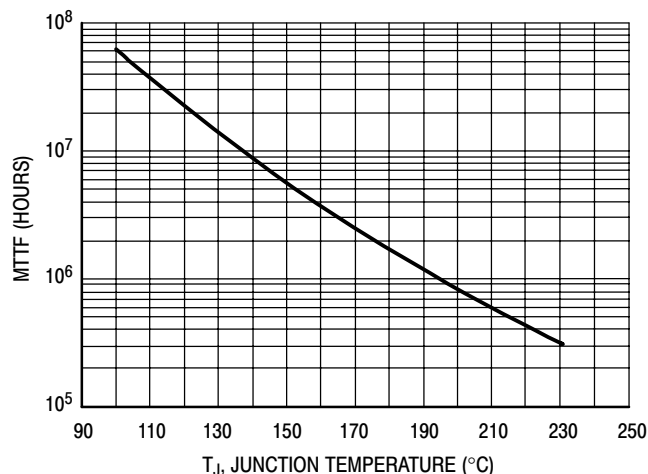


Figure 13. Power Gain versus Output Power



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28$ Vdc, $P_{out} = 10$ W Avg., and $\eta_D = 25.5\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.

Figure 14. MTTF versus Junction Temperature

W-CDMA TEST SIGNAL

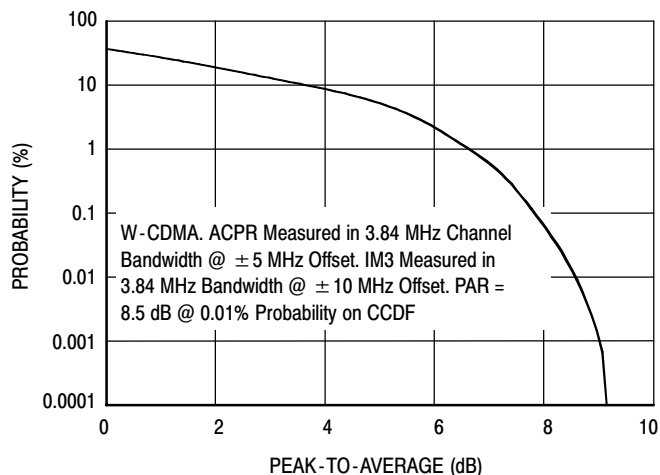


Figure 15. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

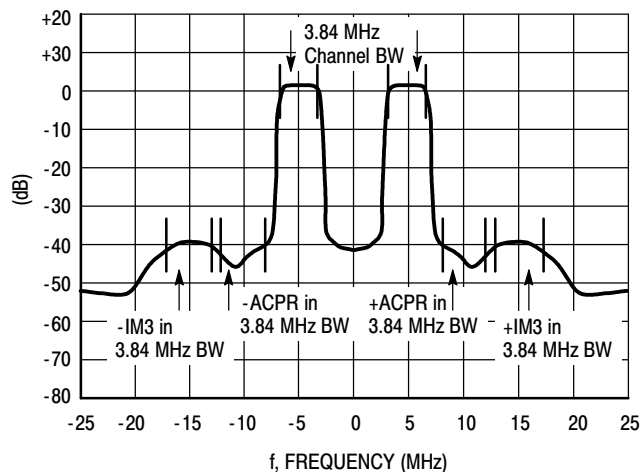
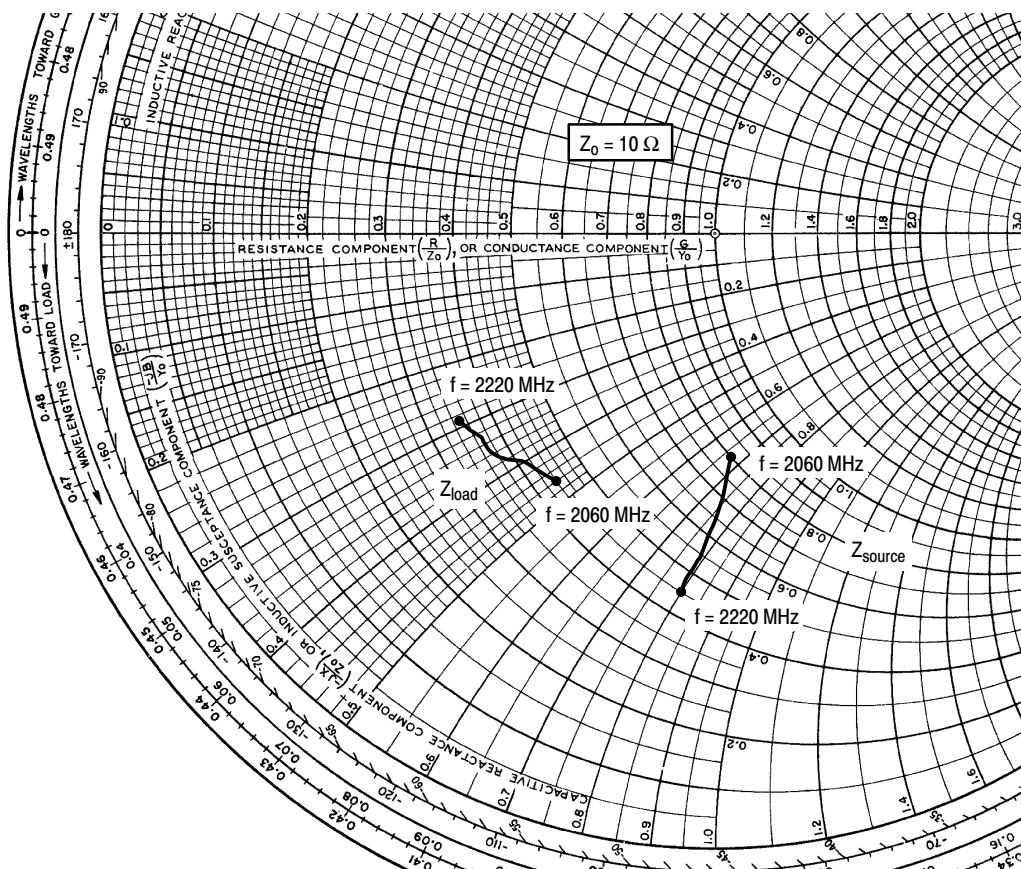


Figure 16. 2-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 500 \text{ mA}$, $P_{out} = 10 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
2060	8.01 - j6.68	4.38 - j4.62
2080	7.66 - j6.94	4.27 - j4.43
2100	7.26 - j7.20	4.12 - j4.04
2120	6.76 - j7.45	3.98 - j3.90
2140	6.28 - j7.71	3.81 - j3.69
2160	5.82 - j7.78	3.73 - j3.50
2180	5.37 - j7.85	3.65 - j3.30
2200	4.92 - j7.85	3.57 - j3.11
2220	4.46 - j7.97	3.49 - j2.92

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

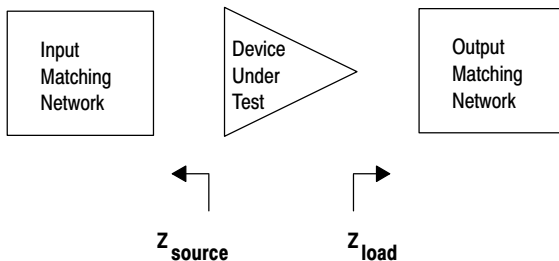
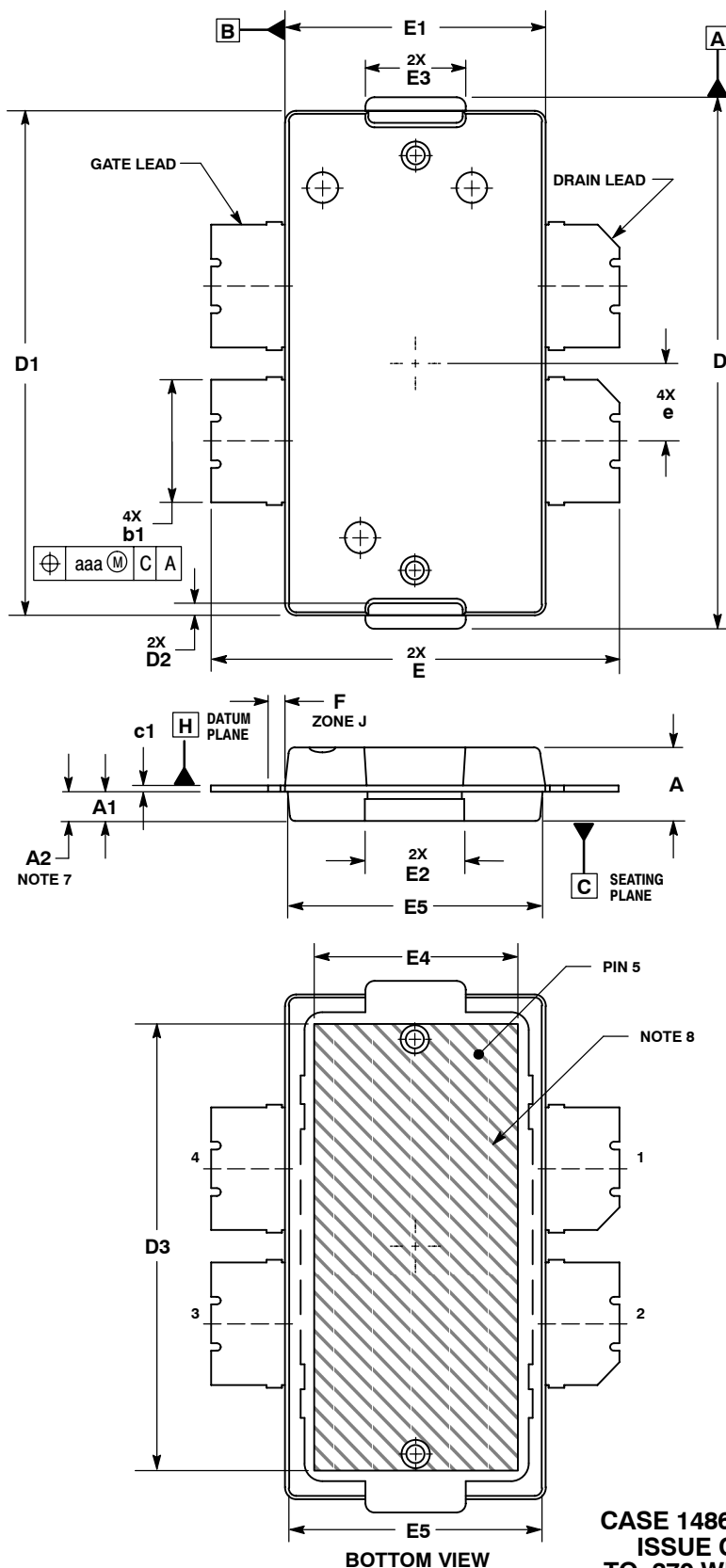


Figure 17. Series Equivalent Source and Load Impedance — Single-Ended Configuration

PACKAGE DIMENSIONS



- NOTES:
1. CONTROLLING DIMENSION: INCH.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
 4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
 5. DIMENSION "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
 7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
 8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.039	.043	0.99	1.09
A2	.040	.042	1.02	1.07
D	.712	.720	18.08	18.29
D1	.688	.692	17.48	17.58
D2	.011	.019	0.28	0.48
D3	.600	---	15.24	---
E	.551	.559	14	14.2
E1	.353	.357	8.97	9.07
E2	.132	.140	3.35	3.56
E3	.124	.132	3.15	3.35
E4	.270	---	6.86	---
E5	.346	.350	8.79	8.89
F	.025 BSC		0.64 BSC	
b1	.164	.170	4.17	4.32
c1	.007	.011	0.18	0.28
e	.106 BSC		2.69 BSC	
aaa	.004		0.10	

- STYLE 1:
- PIN 1. DRAIN
 - DRAIN
 - GATE
 - GATE
 - SOURCE

**CASE 1486-03
ISSUE C
TO-270 WB-4
PLASTIC**

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- AN3263: Bolt Down Mounting Method for High Power RF Transistors and RFICs in Over-Molded Plastic Packages

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	April 2007	• Initial Release of Data Sheet

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